Amendments to the Claims:

- 1-9. (canceled)
- 10. (currently amended) The interconnect structure of Claim <u>25</u> 9, further comprising a hardmask layer overlying the second layer of dielectric material, and wherein the second portion of the second conductor has a top surface coplanar with a top surface of the hardmask layer.
- 11. (currently amended) The interconnect structure of Claim <u>25</u> 9, wherein the second dielectric material is the same as the first dielectric material.
- 12. (currently amended) The interconnect structure of Claim <u>25</u> 9, wherein the second dielectric material is different from the first dielectric material.
- 13. (currently amended) The Interconnect structure of Claim <u>25</u> 8, wherein the second conductor <u>comprises</u> is formed of copper.
- 14. (currently amended) The interconnect structure of Claim <u>25</u> 9, wherein the <u>second first liner comprises a material selected from the group consisting of titanium nitride, tantalum, tantalum nitride and tungsten, and the <u>first second liner comprises a material selected from the group consisting of tantalum nitride and tantalum.</u></u>

10/604,026

FIS920030130US1

15-24. (canceled)

25. (new) An interconnect structure formed on a substrate, the structure comprising:

a first layer of a first dielectric material having at least one first conductor embedded therein, the first conductor having a top surface coplanar with a top surface of the layer of dielectric material;

a second layer of a second dielectric material overlying the first layer of dielectric material and having at least one second conductor embedded therein, the second conductor comprising at least one first portion and at least one second portion, wherein the first portion is in electrical contact with the first conductor, the second portion is overlying and in electrical contact with the first portion, the second portion has a lateral extent greater than that of the first portion, and the second portion has a top surface coplanar with a top surface of the second layer of dielectric material;

a first conductive liner disposed on an underside and sidewalls of the second conductor, and

a second liner disposed on an underside and sidewalls of the first portion of the second conductor.